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Renesas Technology Corp.
Customer Support Dept.
April 1, 2003

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Remember to give due consideration to safety when making your circuit designs, with appropriate measures such as (i) placement of substitutive, auxiliary circuits, (ii) use of nonflammable material or (iii) prevention against any malfunction or mishap.

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HM62W8512B Series

4 M SRAM (512-kword × 8-bit)



ADE-203-904F (Z)
Rev. 5.0
Mar. 15, 2000

Description

The Hitachi HM62W8512B is a 4-Mbit static RAM organized 512-kword × 8-bit. It realizes higher density, higher performance and low power consumption by employing 0.35 μm Hi-CMOS process technology. The device, packaged in a 525-mil SOP (foot print pitch width) or 400-mil TSOP TYPE II is available for high density mounting. The HM62W8512B is suitable for battery backup system.

Features

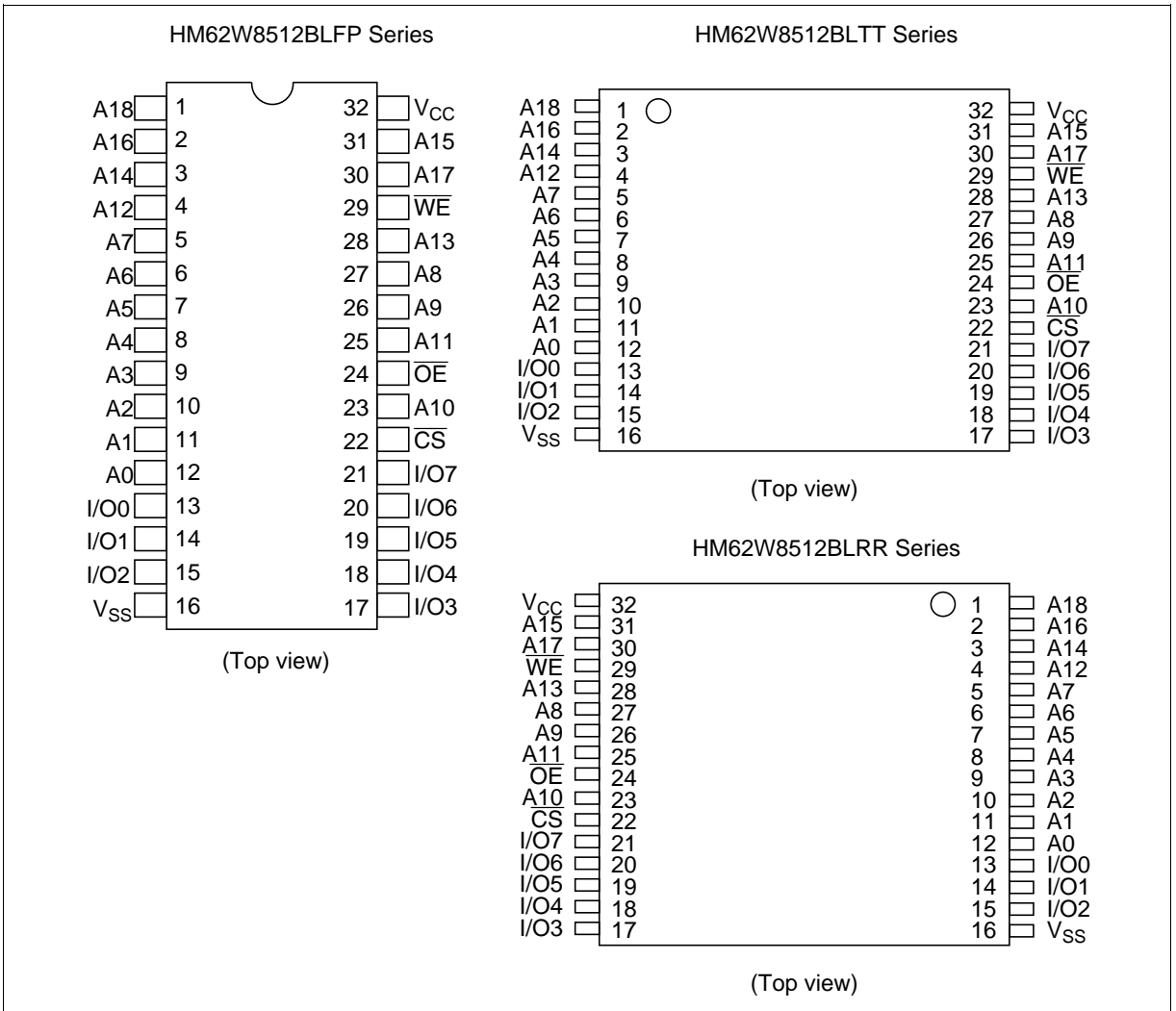
- Single 3.3 V supply: 3.3 V ± 0.3 V
- Access time: 55/70 ns (max)
- Power dissipation
 - Active: 16.5 mW/MHz (typ)
 - Standby: 3.3 μW (typ)
- Completely static memory. No clock or timing strobe required
- Equal access and cycle times
- Common data input and output: Three state output
- Directly LV-TTL compatible: All inputs and outputs
- Battery backup operation

HM62W8512B Series

Ordering Information

| Type No. | Access time | Package |
|-------------------|-------------|---|
| HM62W8512BLFP-5 | 55 ns | 525-mil 32-pin plastic SOP (FP-32D) |
| HM62W8512BLFP-7 | 70 ns | |
| HM62W8512BLFP-5SL | 55 ns | |
| HM62W8512BLFP-7SL | 70 ns | |
| HM62W8512BLFP-5UL | 55 ns | |
| HM62W8512BLFP-7UL | 70 ns | |
| HM62W8512BLTT-5 | 55 ns | 400-mil 32-pin plastic TSOP II (TTP-32D) |
| HM62W8512BLTT-7 | 70 ns | |
| HM62W8512BLTT-5SL | 55 ns | |
| HM62W8512BLTT-7SL | 70 ns | |
| HM62W8512BLTT-5UL | 55 ns | |
| HM62W8512BLTT-7UL | 70 ns | |
| HM62W8512BLRR-5 | 55 ns | 400-mil 32-pin plastic TSOP II reverse (TTP-32DR) |
| HM62W8512BLRR-7 | 70 ns | |
| HM62W8512BLRR-5SL | 55 ns | |
| HM62W8512BLRR-7SL | 70 ns | |
| HM62W8512BLRR-5UL | 55 ns | |
| HM62W8512BLRR-7UL | 70 ns | |

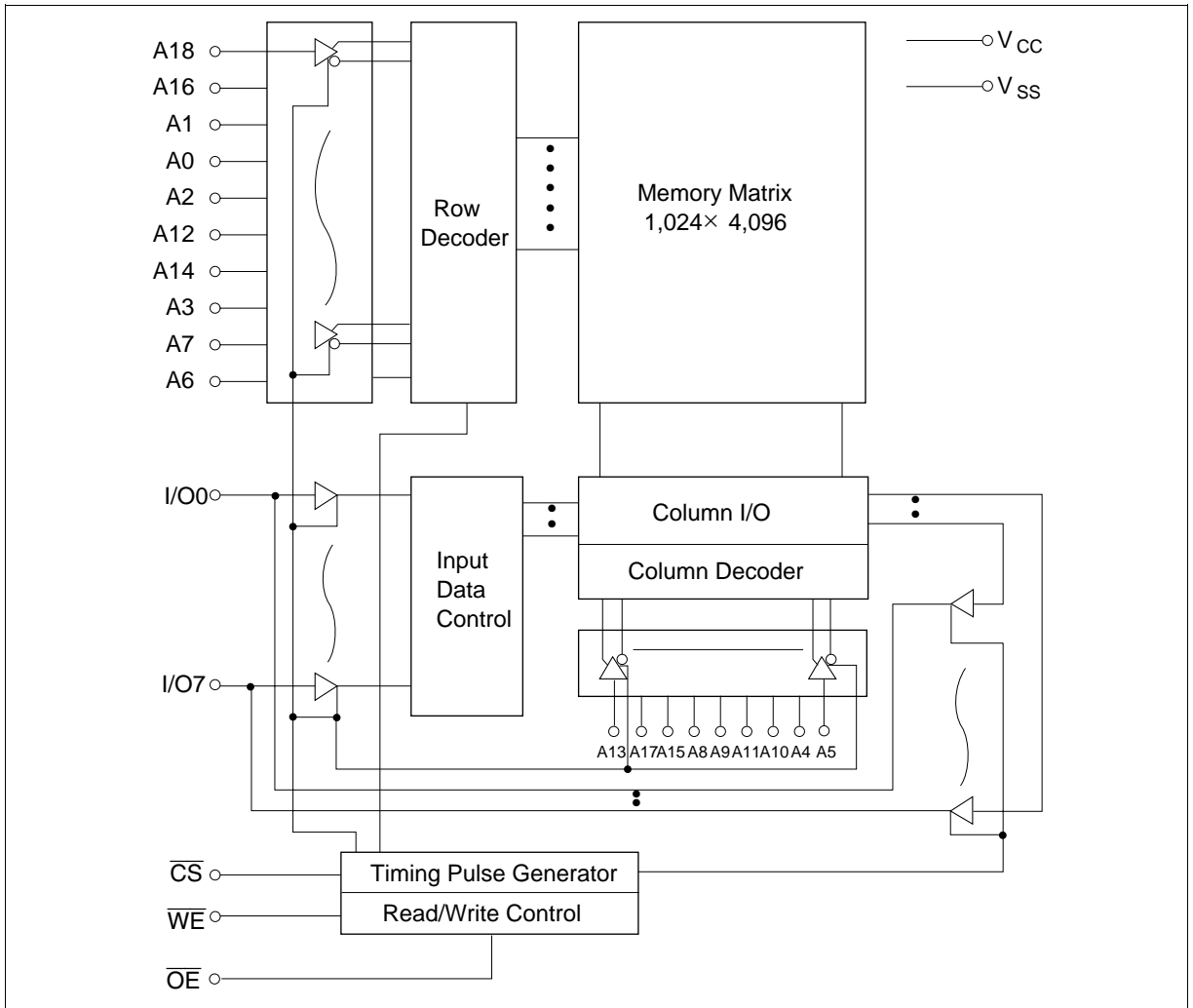
Pin Arrangement



Pin Description

| Pin name | Function |
|-----------------|-------------------|
| A0 to A18 | Address input |
| I/O0 to I/O7 | Data input/output |
| CS | Chip select |
| OE | Output enable |
| WE | Write enable |
| V _{CC} | Power supply |
| V _{SS} | Ground |

Block Diagram



Function Table

| \overline{WE} | \overline{CS} | \overline{OE} | Mode | V_{CC} current | Dout pin | Ref. cycle |
|-----------------|-----------------|-----------------|----------------|-------------------|----------|-----------------|
| x | H | x | Not selected | I_{SB}, I_{SB1} | High-Z | — |
| H | L | H | Output disable | I_{CC} | High-Z | — |
| H | L | L | Read | I_{CC} | Dout | Read cycle |
| L | L | H | Write | I_{CC} | Din | Write cycle (1) |
| L | L | L | Write | I_{CC} | Din | Write cycle (2) |

Note: x: H or L

Absolute Maximum Ratings

| Parameter | Symbol | Value | Unit |
|---|------------|---|------|
| Power supply voltage | V_{CC} | -0.5 to +4.6 | V |
| Voltage on any pin relative to V_{SS} | V_T | -0.5* ¹ to $V_{CC} + 0.5$ * ² | V |
| Power dissipation | P_T | 1.0 | W |
| Operating temperature | T_{opr} | -20 to +70 | °C |
| Storage temperature | T_{stg} | -55 to +125 | °C |
| Storage temperature under bias | T_{bias} | -20 to +85 | °C |

Notes: 1. -3.0 V for pulse half-width \leq 30 ns
 2. Maximum voltage is 4.6 V

Recommended DC Operating Conditions ($T_a = -20$ to +70°C)

| Parameter | Symbol | Min | Typ | Max | Unit |
|--------------------|----------|--------------------|-----|----------------|------|
| Supply voltage | V_{CC} | 3.0 | 3.3 | 3.6 | V |
| | V_{SS} | 0 | 0 | 0 | V |
| Input high voltage | V_{IH} | 2.0 | — | $V_{CC} + 0.3$ | V |
| Input low voltage | V_{IL} | -0.3* ¹ | — | 0.8 | V |

Note: 1. -3.0 V for pulse half-width \leq 30 ns

HM62W8512B Series

DC Characteristics (Ta = -20 to +70°C, V_{CC} = 3.3 V ± 0.3 V, V_{SS} = 0 V)

| Parameter | Symbol | Min | Typ* ¹ | Max | Unit | Test conditions | |
|--------------------------------------|-------------------------------|-----------------------|-------------------|------------------|------------------|--|--|
| Input leakage current | I _{LI} | — | — | 1 | μA | V _{in} = V _{SS} to V _{CC} | |
| Output leakage current | I _{LO} | — | — | 1 | μA | $\overline{CS} = V_{IH}$ or $\overline{OE} = V_{IH}$ or $\overline{WE} = V_{IL}$, V _{I/O} = V _{SS} to V _{CC} | |
| Operating power supply current: DC | I _{CC} | — | — | 10 | mA | $\overline{CS} = V_{IL}$, others = V _{IH} /V _{IL} , I _{I/O} = 0 mA | |
| Operating power supply current | HM62W8512B-5 I _{CC1} | — | — | 45 | mA | Min cycle, duty = 100% $\overline{CS} = V_{IL}$, others = V _{IH} /V _{IL} I _{I/O} = 0 mA | |
| | HM62W8512B-7 I _{CC1} | — | — | 40 | mA | | |
| Operating power supply current | I _{CC2} | — | 5 | 10 | mA | Cycle time = 1 μs, duty = 100% I _{I/O} = 0 mA, $\overline{CS} \leq 0.2$ V V _{IH} ≥ V _{CC} - 0.2 V, V _{IL} ≤ 0.2 V | |
| Standby power supply current: DC | I _{SB} | — | 0.1 | 0.3 | mA | $\overline{CS} = V_{IH}$ | |
| Standby power supply current (1): DC | I _{SB1} | — | 1* ² | 40* ² | μA | V _{in} ≥ 0 V, $\overline{CS} \geq V_{CC} - 0.2$ V | |
| | | | — | 1* ³ | 20* ³ | μA | |
| | | | — | 1* ⁴ | 5* ⁴ | μA | |
| Output low voltage | V _{OL} | — | — | 0.4 | V | I _{OL} = 2.0 mA | |
| | | | | 0.2 | V | I _{OL} = 100 μA | |
| Output high voltage | V _{OH} | V _{CC} - 0.2 | — | — | V | I _{OH} = -100 μA | |
| | | 2.4 | — | — | V | I _{OH} = -2.0 mA | |

- Notes: 1. Typical values are at V_{CC} = 3.3 V, Ta = +25°C and specified loading, and not guaranteed.
 2. This characteristics is guaranteed only for L version.
 3. This characteristics is guaranteed only for L-SL version.
 4. This characteristics is guaranteed only for L-UL version.

Capacitance (Ta = +25°C, f = 1 MHz)

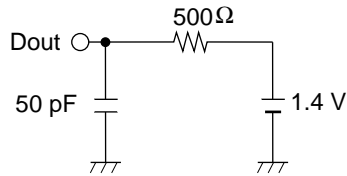
| Parameter | Symbol | Typ | Max | Unit | Test conditions |
|--|------------------|-----|-----|------|------------------------|
| Input capacitance* ¹ | C _{in} | — | 8 | pF | V _{in} = 0 V |
| Input/output capacitance* ¹ | C _{I/O} | — | 10 | pF | V _{I/O} = 0 V |

Note: 1. This parameter is sampled and not 100% tested.

AC Characteristics ($T_a = -20$ to $+70^\circ\text{C}$, $V_{CC} = 3.3\text{ V} \pm 0.3\text{ V}$, unless otherwise noted.)

Test Conditions

- Input pulse levels: 0.4 V to 2.4 V
- Input rise and fall time: 5 ns
- Input timing reference levels: 1.4 V
- Output timing reference level: 1.4 V/1.4 V(HM62W8512B-5)
0.8 V/2.0 V(HM62W8512B-7)
- Output load (Including scope & jig)



Read Cycle

HM62W8512B

| | | -5 | -7 |
|--|--|----|----|
|--|--|----|----|

| Parameter | Symbol | HM62W8512B | | | | Unit | Notes |
|--------------------------------------|-----------|------------|-----|-----|-----|------|-------|
| | | Min | Max | Min | Max | | |
| Read cycle time | t_{RC} | 55 | — | 70 | — | ns | |
| Address access time | t_{AA} | — | 55 | — | 70 | ns | |
| Chip select access time | t_{CO} | — | 55 | — | 70 | ns | |
| Output enable to output valid | t_{OE} | — | 30 | — | 35 | ns | |
| Chip selection to output in low-Z | t_{LZ} | 10 | — | 10 | — | ns | 2 |
| Output enable to output in low-Z | t_{OLZ} | 5 | — | 5 | — | ns | 2 |
| Chip deselection to output in high-Z | t_{HZ} | 0 | 20 | 0 | 30 | ns | 1, 2 |
| Output disable to output in high-Z | t_{OHZ} | 0 | 20 | 0 | 30 | ns | 1, 2 |
| Output hold from address change | t_{OH} | 10 | — | 10 | — | ns | |

Write Cycle

| Parameter | Symbol | HM62W8512B | | | | Unit | Notes |
|-------------------------------------|-----------|------------|-----|-----|-----|------|---------|
| | | -5 | | -7 | | | |
| | | Min | Max | Min | Max | | |
| Write cycle time | t_{WC} | 55 | — | 70 | — | ns | |
| Chip selection to end of write | t_{CW} | 50 | — | 60 | — | ns | 4 |
| Address setup time | t_{AS} | 0 | — | 0 | — | ns | 5 |
| Address valid to end of write | t_{AW} | 50 | — | 60 | — | ns | |
| Write pulse width | t_{WP} | 40 | — | 50 | — | ns | 3, 12 |
| Write recovery time | t_{WR} | 0 | — | 0 | — | ns | 6 |
| \overline{WE} to output in high-Z | t_{WHZ} | 0 | 20 | 0 | 30 | ns | 1, 2, 7 |
| Data to write time overlap | t_{DW} | 25 | — | 30 | — | ns | |
| Data hold from write time | t_{DH} | 0 | — | 0 | — | ns | |
| Output active from output in high-Z | t_{OW} | 5 | — | 5 | — | ns | 2 |
| Output disable to output in high-Z | t_{OHZ} | 0 | 20 | 0 | 30 | ns | 1, 2, 7 |

Notes: 1. t_{HZ} , t_{OHZ} and t_{WHZ} are defined as the time at which the outputs achieve the open circuit conditions and are not referred to output voltage levels.

2. This parameter is sampled and not 100% tested.

3. A write occurs during the overlap (t_{WP}) of a low \overline{CS} and a low \overline{WE} . A write begins at the later transition of \overline{CS} going low or \overline{WE} going low. A write ends at the earlier transition of \overline{CS} going high or \overline{WE} going high. t_{WP} is measured from the beginning of write to the end of write.

4. t_{CW} is measured from \overline{CS} going low to the end of write.

5. t_{AS} is measured from the address valid to the beginning of write.

6. t_{WR} is measured from the earlier of \overline{WE} or \overline{CS} going high to the end of write cycle.

7. During this period, I/O pins are in the output state so that the input signals of the opposite phase to the outputs must not be applied.

8. If the \overline{CS} low transition occurs simultaneously with the \overline{WE} low transition or after the \overline{WE} transition, the output remain in a high impedance state.

9. Dout is the same phase of the write data of this write cycle.

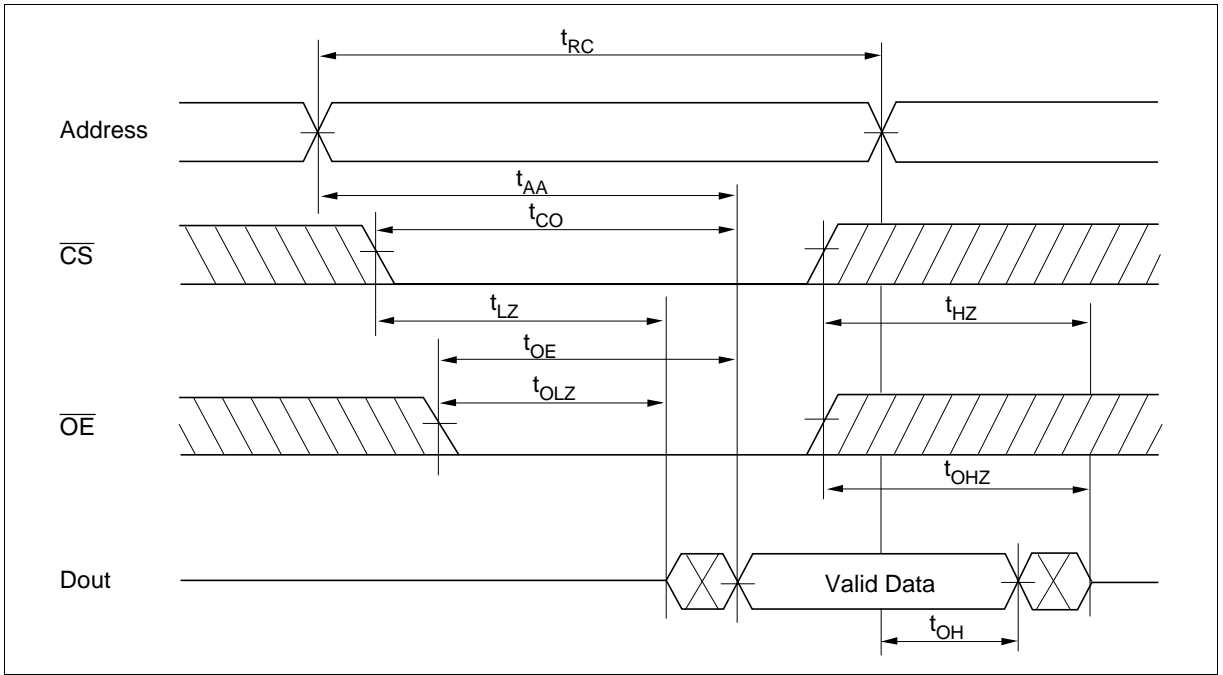
10. Dout is the read data of next address.

11. If \overline{CS} is low during this period, I/O pins are in the output state. Therefore, the input signals of the opposite phase to the outputs must not be applied to them.

12. In the write cycle with \overline{OE} low fixed, t_{WP} must satisfy the following equation to avoid a problem of data bus contention. $t_{WP} \geq t_{DW} \text{ min} + t_{WHZ} \text{ max}$

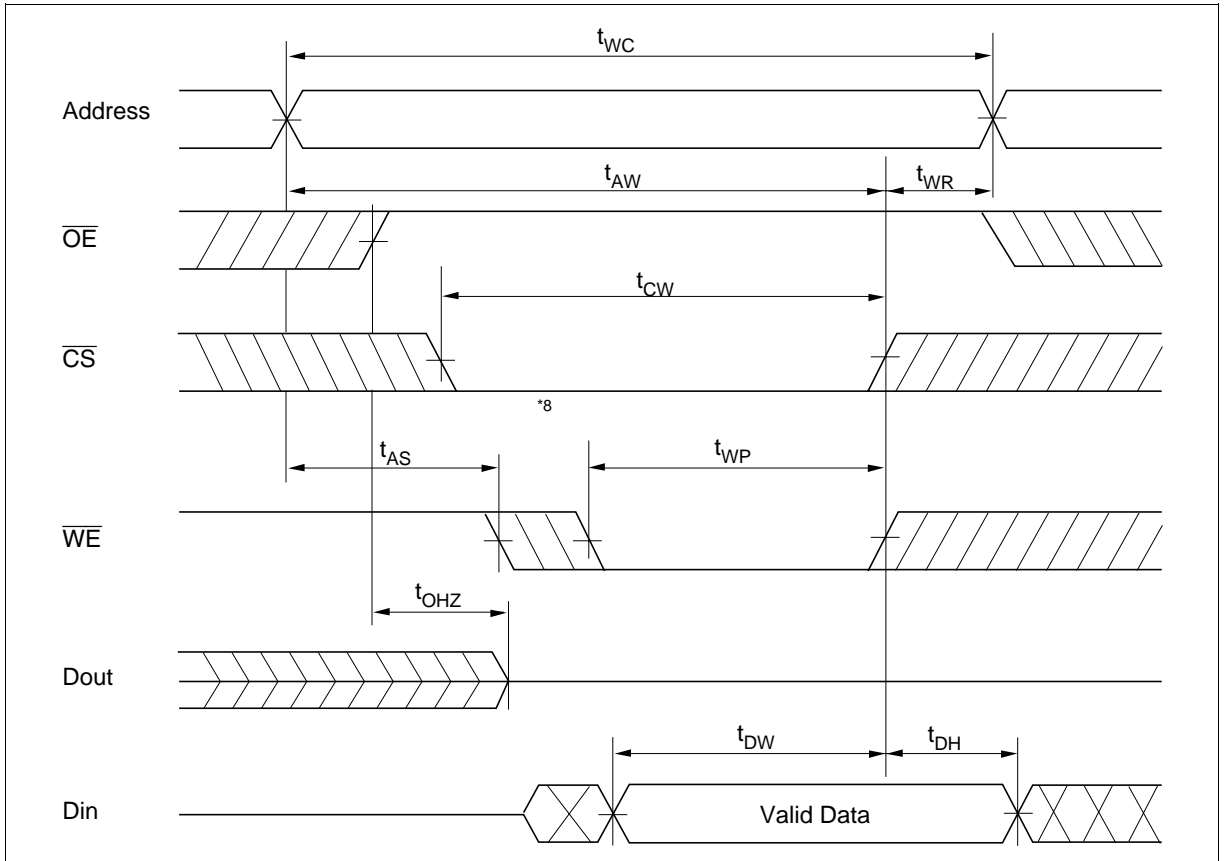
Timing Waveforms

Read Timing Waveform ($\overline{WE} = V_{IH}$)

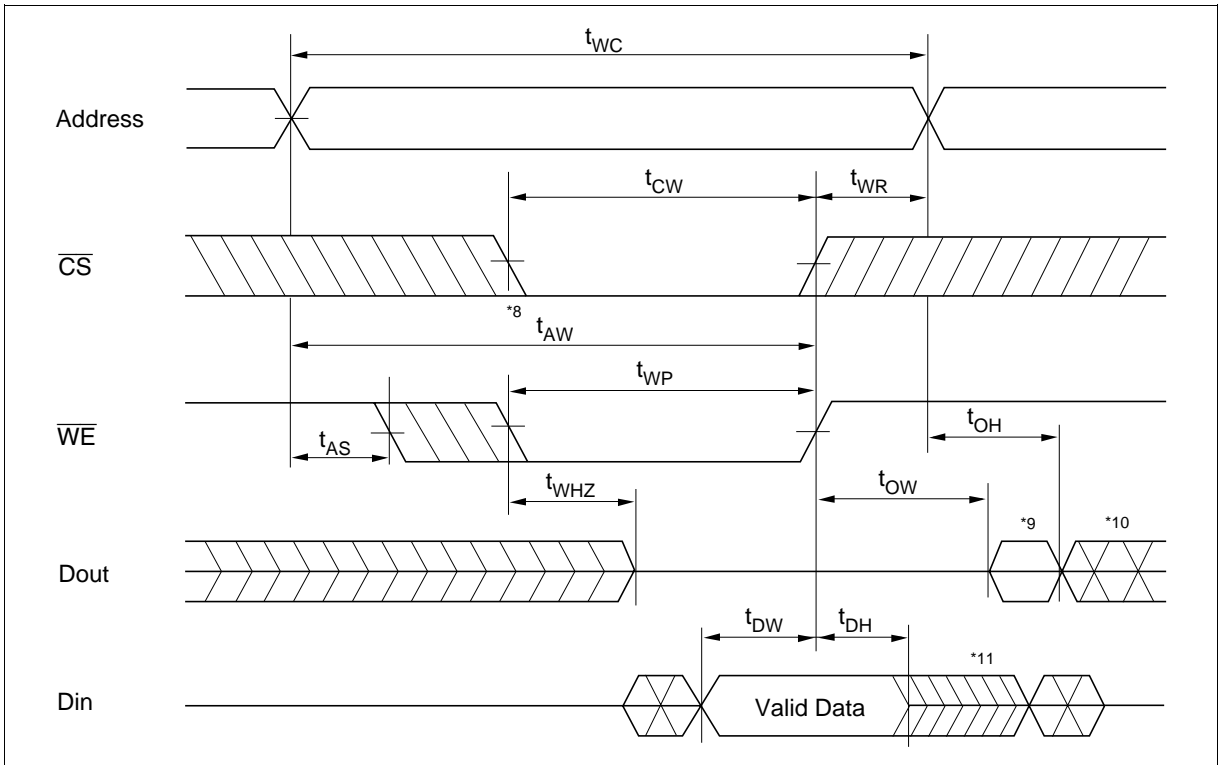


HM62W8512B Series

Write Timing Waveform (1) (\overline{OE} Clock)



Write Timing Waveform (2) (\overline{OE} Low Fixed)

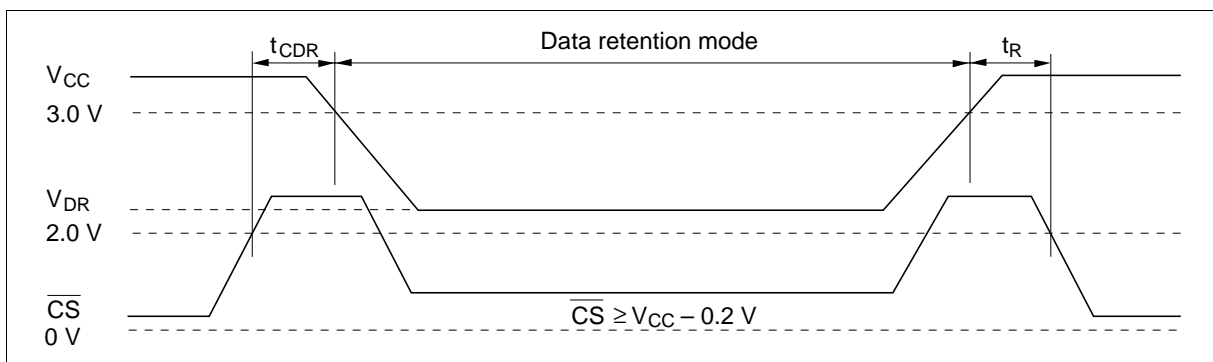


Low V_{CC} Data Retention Characteristics ($T_a = -20$ to $+70^\circ\text{C}$)

| Parameter | Symbol | Min | Typ | Max | Unit | Test conditions**4 |
|--------------------------------------|------------|---------------|------------|-----------|---------------|--|
| V_{CC} for data retention | V_{DR} | 2 | — | — | V | $\overline{CS} \geq V_{CC} - 0.2\text{ V}$, $V_{in} \geq 0\text{ V}$ |
| Data retention current | I_{CCDR} | — | 0.8^{*5} | 20^{*1} | μA | $V_{CC} = 3.0\text{ V}$, $V_{in} \geq 0\text{ V}$ $\overline{CS} \geq V_{CC} - 0.2\text{ V}$ |
| | | — | 0.8^{*5} | 10^{*2} | μA | |
| | | — | 0.8^{*5} | 2^{*3} | μA | |
| Chip deselect to data retention time | t_{CDR} | 0 | — | — | ns | See retention waveform |
| Operation recovery time | t_R | t_{RC}^{*6} | — | — | ns | |

- Notes:
1. For L-version and $10\ \mu\text{A}$ (max.) at $T_a = -20$ to $+40^\circ\text{C}$.
 2. For L-SL-version and $3\ \mu\text{A}$ (max.) at $T_a = -20$ to $+40^\circ\text{C}$.
 3. For L-UL-version and $2\ \mu\text{A}$ (max.) at $T_a = -20$ to $+40^\circ\text{C}$.
 4. \overline{CS} controls address buffer, \overline{WE} buffer, \overline{OE} buffer, and D_{in} buffer. In data retention mode, V_{in} levels (address, \overline{WE} , \overline{OE} , I/O) can be in the high impedance state.
 5. Typical values are at $V_{CC} = 3.0\text{ V}$, $T_a = +25^\circ\text{C}$ and specified loading, and not guaranteed.
 6. t_{RC} = read cycle time.

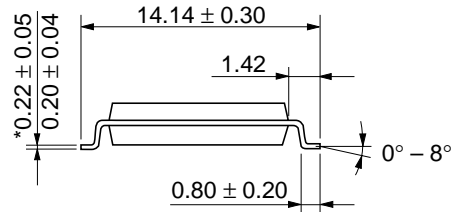
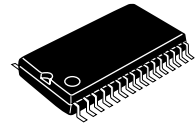
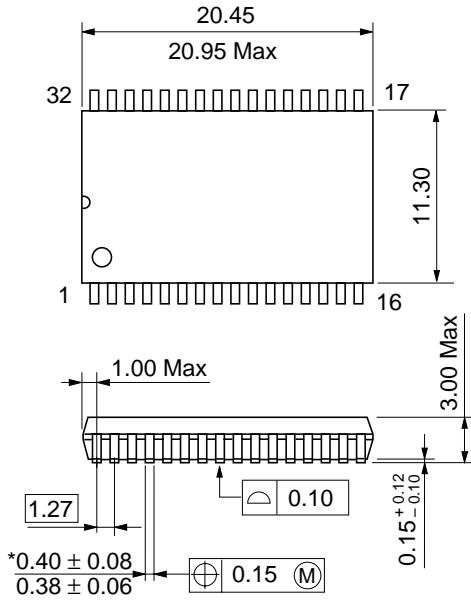
Low V_{CC} Data Retention Timing Waveform (\overline{CS} Controlled)



Package Dimensions

HM62W8512BLFP Series (FP-32D)

Unit: mm



* 0.40 ± 0.08
 0.38 ± 0.06

$\oplus 0.15$ (M)

*Dimension including the plating thickness
Base material dimension

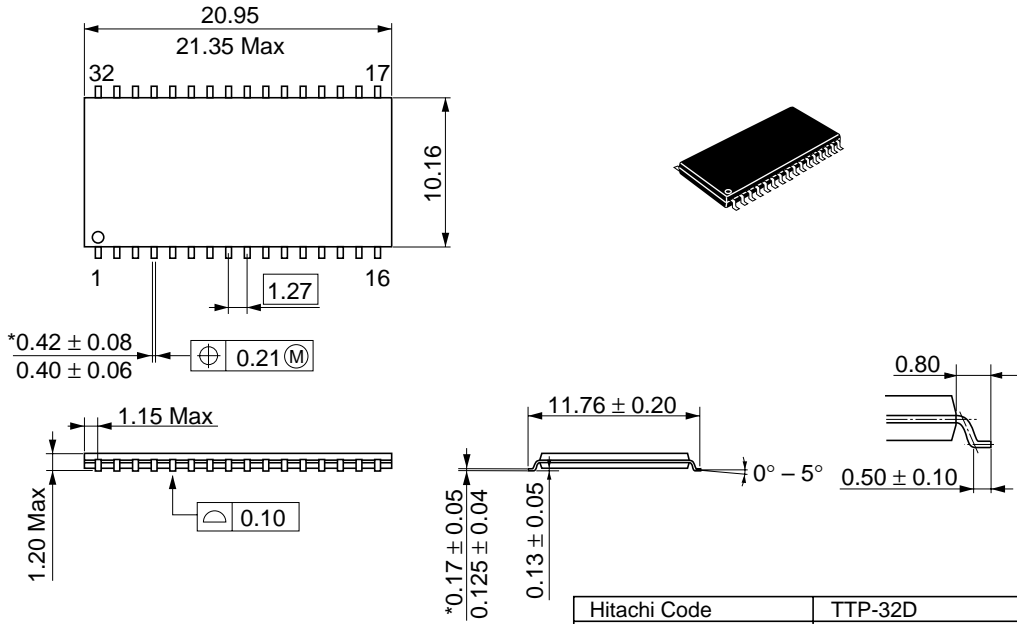
| | |
|--------------------------|----------|
| Hitachi Code | FP-32D |
| JEDEC | Conforms |
| EIAJ | — |
| Weight (reference value) | 1.3 g |

HM62W8512B Series

Package Dimensions (cont.)

HM62W8512BLTT Series (TTP-32D)

Unit: mm



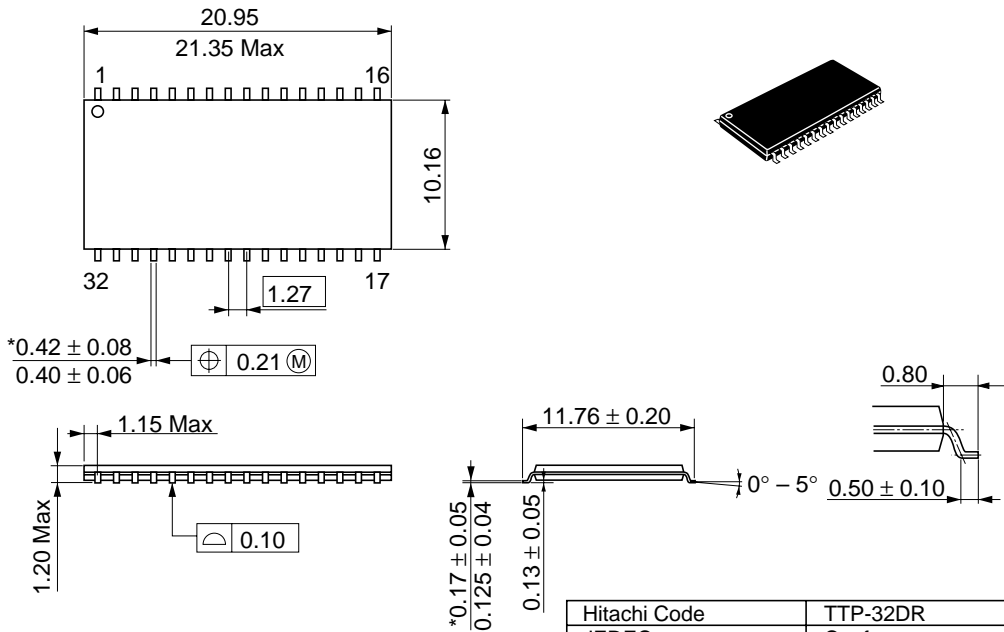
*Dimension including the plating thickness
Base material dimension

| | |
|--------------------------|----------|
| Hitachi Code | TTP-32D |
| JEDEC | Conforms |
| EIAJ | — |
| Weight (reference value) | 0.51 g |

Package Dimensions (cont.)

HM62W8512BLRR Series (TTP-32DR)

Unit: mm



*Dimension including the plating thickness
Base material dimension

| | |
|--------------------------|----------|
| Hitachi Code | TTP-32DR |
| JEDEC | Conforms |
| EIAJ | — |
| Weight (reference value) | 0.51 g |

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